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Vishay Siliconix

Automotive P-Channel 20 V (D-S) 175 °C MOSFET



Marking Code: 9GYXX

PRODUCT SUMMARY					
V _{DS} (V)	-20				
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5 \text{ V}$	0.125				
$R_{DS(on)}$ (Ω) at $V_{GS} = -2.5 \text{ V}$	0.215				
I _D (A)	-3.1				
Configuration	Single				
Package	SOT-23				

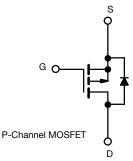
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified d
- 100 % Rg and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



HALOGEN

FREE



ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2391ES (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-20	V	
Gate-source voltage		V _{GS}	± 12	V	
Continuous drain current	T _C = 25 °C	- I _D	-3.1		
	T _C = 125 °C		-1.8		
Continuous source current (diode conduction) a	Is	-2.5	Α		
Pulsed drain current ^b		I _{DM}	-12.7		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-6		
Single pulse avalanche energy	L=0.11IIII	E _{AS}	1.8	mJ	
Maximum power dissipation ^b	T _C = 25 °C	P _D	2	W	
	T _C = 125 °C		0.67	VV	
Operating junction and storage temperature rang	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R _{thJA}	175	°C/W
Junction-to-foot (drain)		R_{thJF}	75	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static		•				I.	<u> </u>
Drain-source breakdown voltage	V _{DS}	V_{GS}	$V_{GS} = 0, I_{D} = -250 \mu A$		-	-	.,
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-1.0	-1.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = -20 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -20 V, T _J = 125 °C	-	-	-50	μΑ
		$V_{GS} = 0 V$	V _{DS} = -20 V, T _J = 175 °C	-	-	-150	1
On-state drain current ^a	I _{D(on)}	V _{GS} = -4.5 V	$V_{DS} \ge 5 V$	-8	-	-	Α
		$V_{GS} = -4.5 \text{ V}$	I _D = -2.4 A	-	0.085	0.125	Ω
Duning and the second of the s	Б	V _{GS} = -4.5 V	I _D = -2.4 A, T _J = 125 °C	-	-	0.175	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -2.4 A, T _J = 175 °C	-	-	0.200	
		V _{GS} = -2.5 V	I _D = -1.8 A	-	0.160	0.215	
Forward transconductance b	9 _{fs}	V _{DS} =	-10 V, I _D = -2.4 A	-	6	-	S
Dynamic ^b	_						
Input capacitance	C _{iss}			-	265	330	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = -10 \text{ V, f} = 1 \text{ MHz}$	-	75	94	pF
Reverse transfer capacitance	C _{rss}			-	50	63	
Total gate charge c	Q_g			-	3.4	5.5	
Gate-source charge ^c	Q _{gs}	$V_{GS} = -4.5 \text{ V}$	$V_{DS} = -10 \text{ V}, I_{D} = -2.4 \text{ A}$	-	0.6	-	nC
Gate-drain charge ^c	Q _{gd}			-	1.1	-	
Gate resistance	R_g	f = 1 MHz		4.8	9.6	14.4	Ω
Turn-on delay time ^c	t _{d(on)}			-	20	30	
Rise time ^c	t _r	V_{DD} = -10 V, R_L = 5.21 Ω I_D \cong -1.9 A, V_{GEN} = -4.5 V, R_g = 1 Ω		-	18	27	
Turn-off delay time ^c	t _{d(off)}			-	19	28	ns
Fall time ^c	t _f			-	8	12	
Source-Drain Diode Ratings and Char	acteristics						
Pulsed current ^a	I _{SM}				-	-12.7	Α
Forward voltage	V _{SD}	I _F = -2 A, V _{GS} = 0			-0.8	-1.2	V

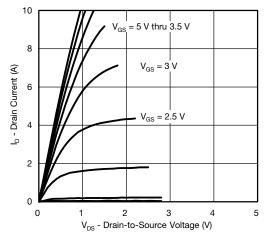
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

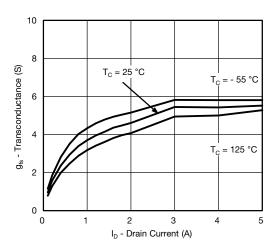
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



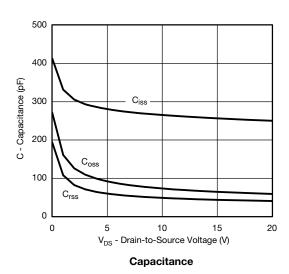
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

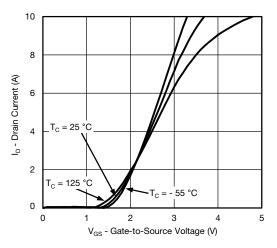


Output Characteristics

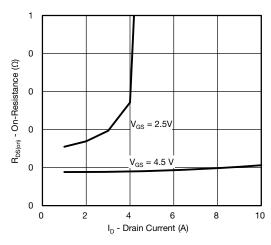


Transconductance

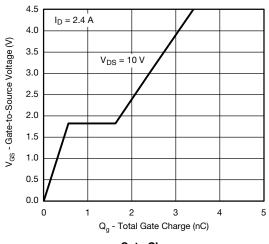




Transfer Characteristics

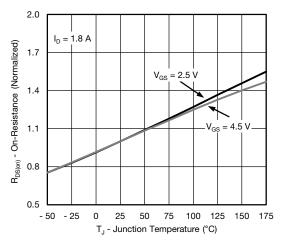


On-Resistance vs. Drain Current

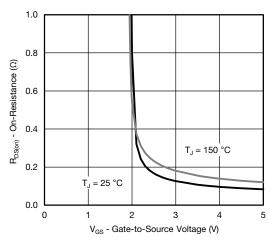




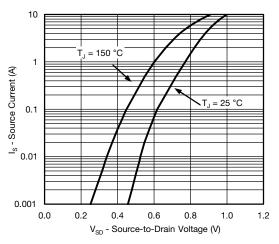
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



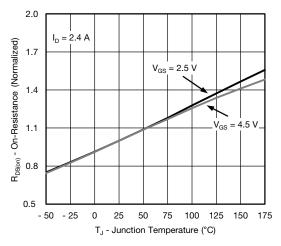
On-Resistance vs. Junction Temperature (1.8 V)



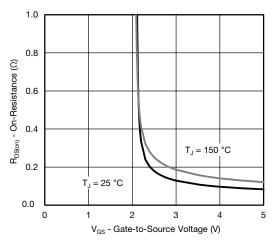
On-Resistance vs. Gate-to-Source Voltage (1.8 V)



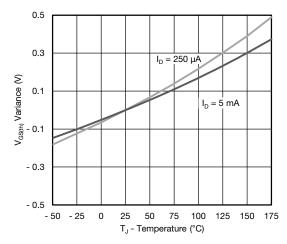
Source-Drain Diode Forward Voltage



On-Resistance vs. Junction Temperature (2.4 V)



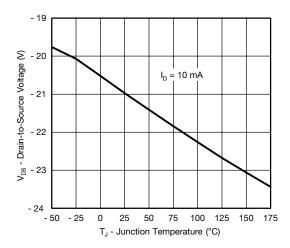
On-Resistance vs. Gate-to-Source Voltage (2.4 V)



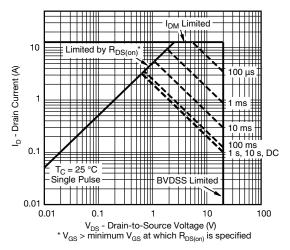
Threshold Voltage



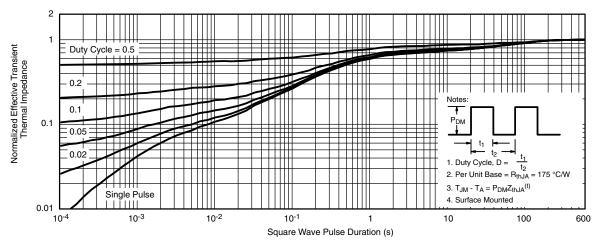
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Drain Source Breakdown vs. Junction Temperature



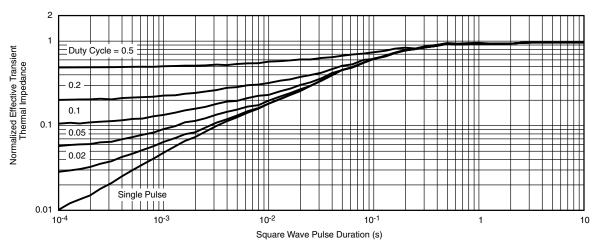
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg275141.



SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	i Ref	
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479

Document Number: 71196 www.vishay.com 09-Jul-01



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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